

## ABBREVIATED DESCRIPTION

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### **METHOD FOR MODIFICATION OF INSULATING, SEMICONDUCTOR OR METALLIC SURFACES, AND PRODUCTS THUS OBTAINED**

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The present invention relates to the use of a  $R-N_2^+$  diazonium salt carrying an aromatic group R, for the grafting of the said aromatic group onto insulating, semiconductor, binary or ternary compound or composite material surfaces, the said diazonium salt being present at a concentration close to its solubility limit, notably at a concentration higher than 0.05 M, and preferably varying between approximately 0.5 M

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to approximately 4 M.

(no Figure)